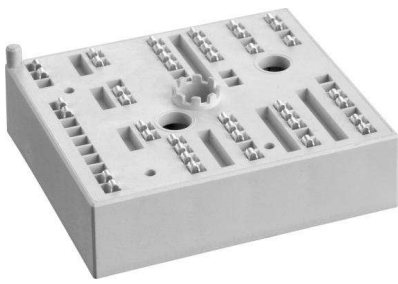


SKiiP 24NAB126V10



MiniSKiiP® 2

3-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 24NAB126V10

Features

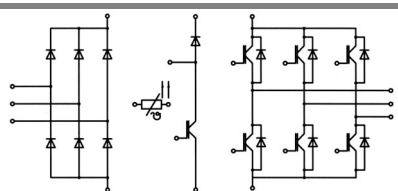
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 19 kVA
- Typical motor power 11 kW

Remarks

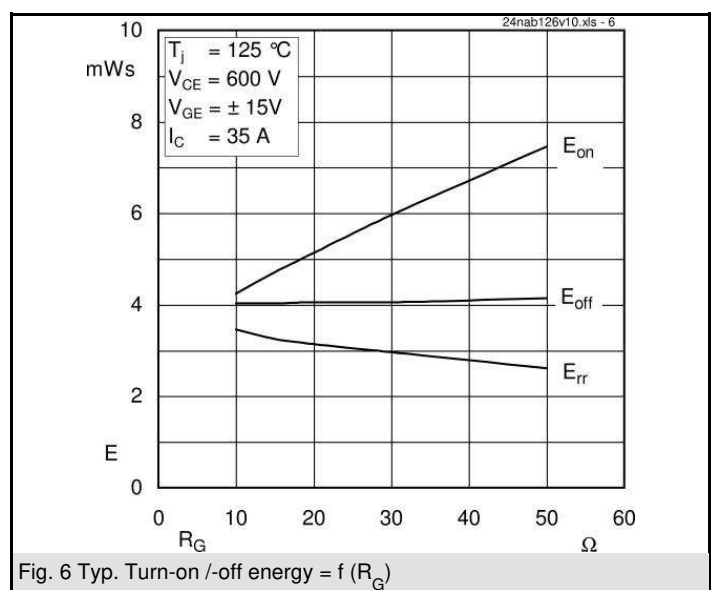
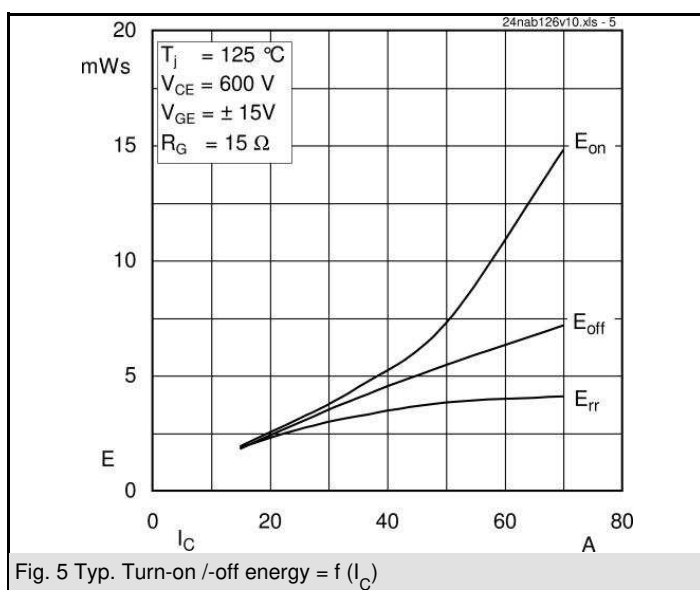
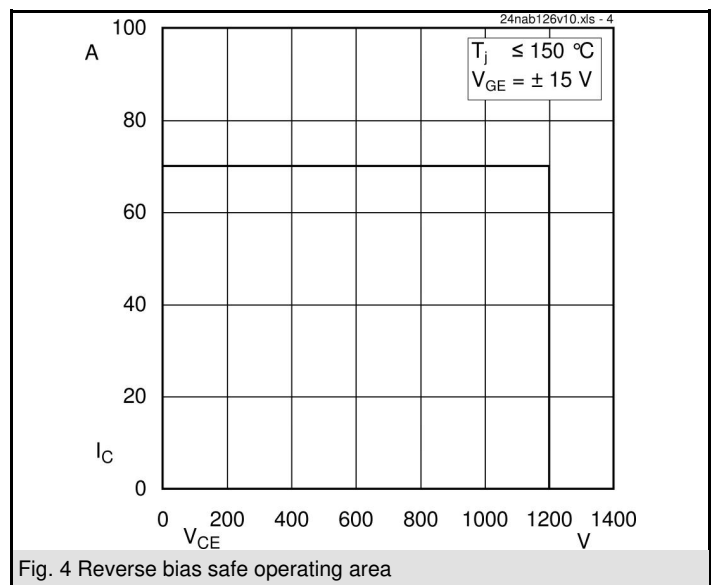
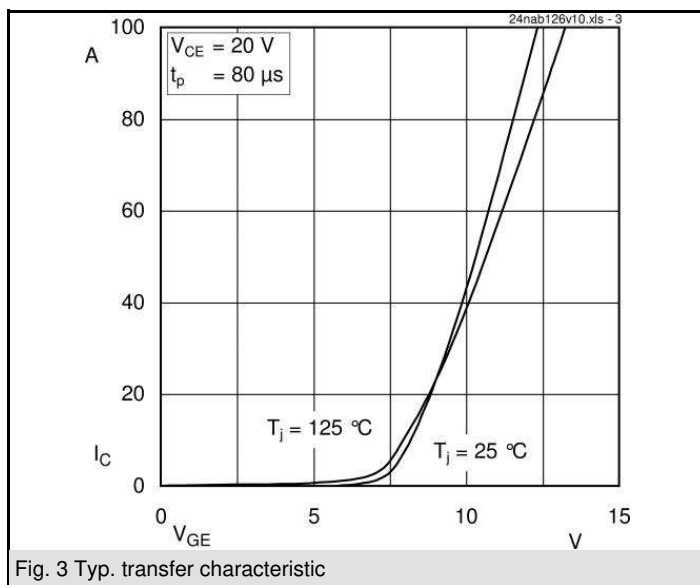
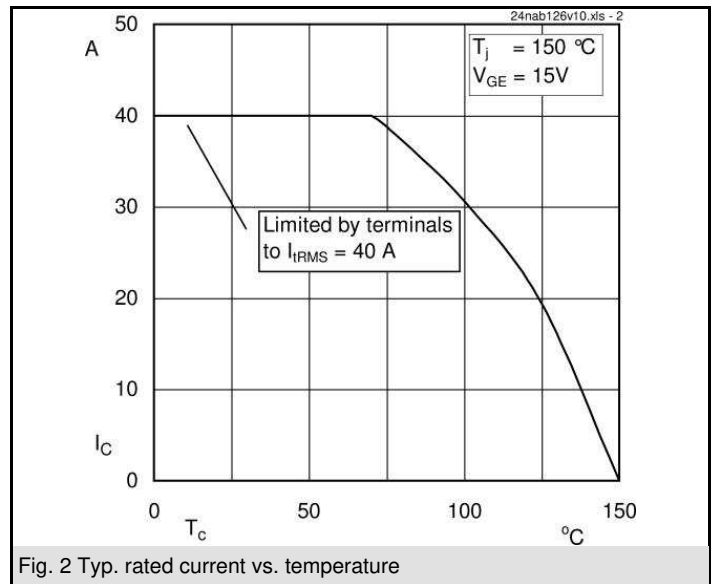
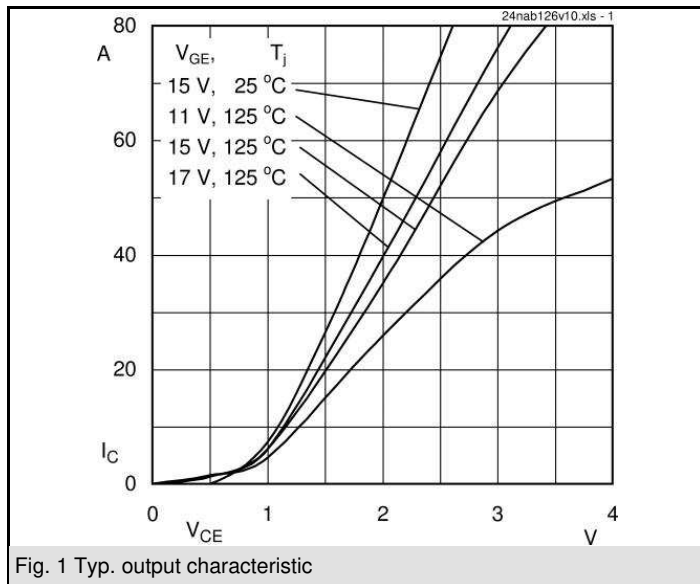
- V_{CEsat} , V_F = chip level value



NAB

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V _{CES}	T _s = 25 (70) °C	1200	V
I _C		52 (40)	A
I _{CRM}		70	A
V _{GES}		± 20	V
T _j		- 40 ... + 150	°C
Diode - Inverter, Chopper			
I _F	T _s = 25 (70) °C	38 (29)	A
I _{FRM}		70	A
T _j		- 40 ... + 150	°C
Diode - Rectifier			
V _{RRM}	T _s = 70 °C	1600	V
I _F		61	A
I _{FSM}		700	A
i ² t		2400	A²s
T _j		- 40 ... + 150	°C
Module			
I _{tRMS}	per power terminal (20 A / spring)	40	A
T _{stg}		- 40 ... + 125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics		T _s = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
V _{CEsat}	I _{Cnom} = 35 A, T _j = 25 (125) °C	5	1,7 (2)	2,1 (2,4)	V
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 1,5 mA		5,8	6,5	V
V _{CE(TO)}	T _j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V
r _T	T _j = 25 (125) °C		20 (31)	26 (37)	mΩ
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		2,4		nF
C _{oes}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,5		nF
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,3		nF
R _{th(j-s)}	per IGBT		0,75		K/W
t _{d(on)}	under following conditions		80		ns
t _r	V _{CC} = 600 V, V _{GE} = ± 15 V		30		ns
t _{d(off)}	I _{Cnom} = 35 A, T _j = 125°C		410		ns
t _f	R _{Gon} = R _{Goff} = 15 Ω		120		ns
E _{on}	inductive load		4,6		mJ
E _{off}			4		mJ
Diode - Inverter, Chopper					
V _F = V _{EC}	I _{Fnom} = 35 A, T _j = 25 (125) °C		1,8 (1,8)	2,1 (2,2)	V
V _(TO)	T _j = 25 (125) °C		1 (0,8)	1,1 (0,9)	V
r _T	T _j = 25 (125) °C		23 (31)	29 (37)	mΩ
R _{th(j-s)}	per diode		1,5		K/W
I _{RRM}	under following conditions		43		A
Q _{rr}	I _{Fnom} = 35 A, V _R = 600 V		7		μC
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		3,3		mJ
	di _F /dt = 1450 A/μs				
Diode -Rectifier					
V _F	I _{Fnom} = 35 A, T _j = 25 °C		1,1		V
V _(TO)	T _j = 150 °C		0,8		V
r _T	T _j = 150 °C		11		mΩ
R _{th(j-s)}	per diode		0,9		K/W
Temperature Sensor					
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω
Mechanical Data					
w			65		g
M _s	Mounting torque	2		2,5	Nm



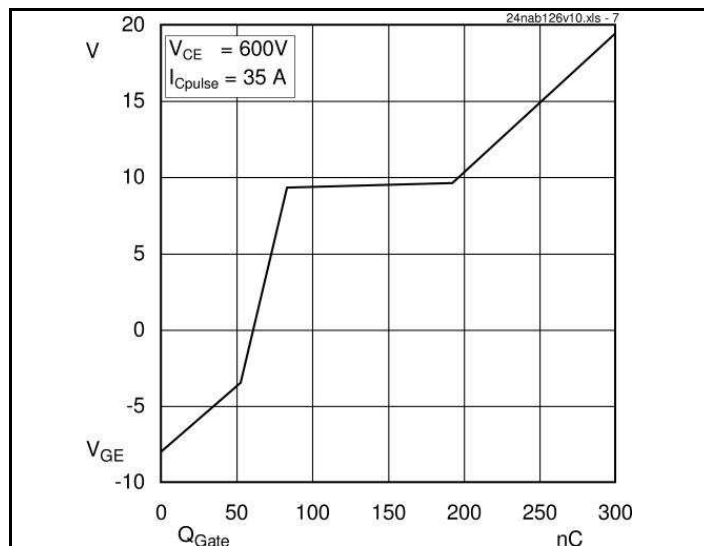


Fig. 7 Typ. gate charge characteristic

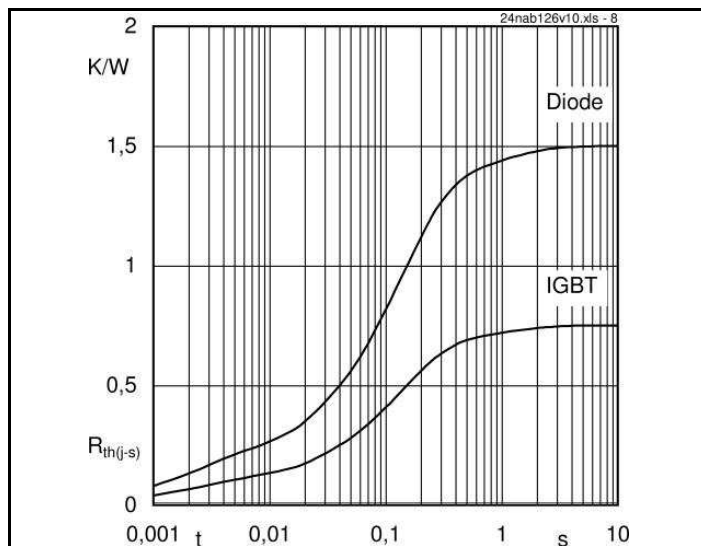


Fig. 8 Typ. thermal impedance

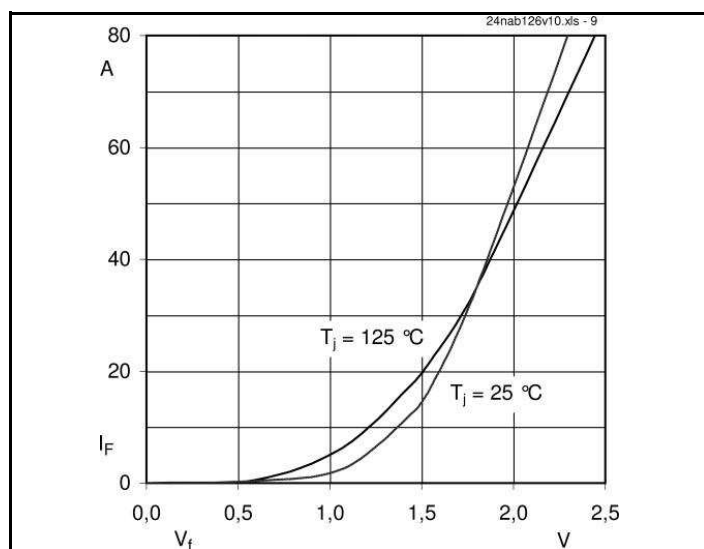


Fig. 9 Typ. freewheeling diode forward characteristic

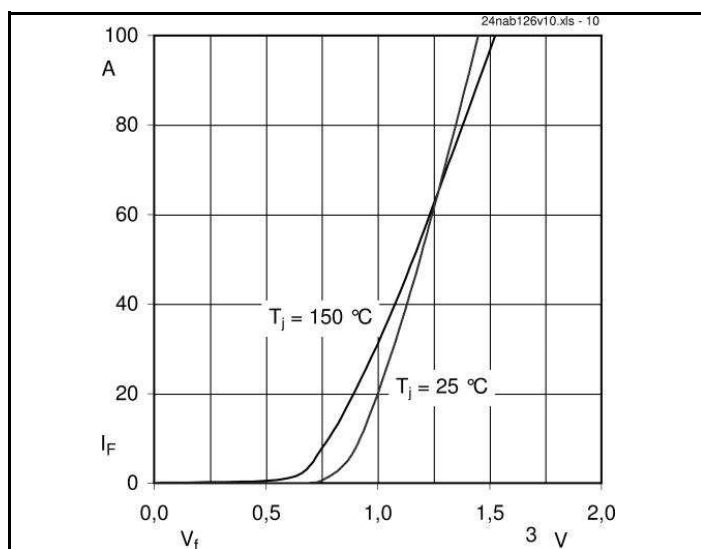
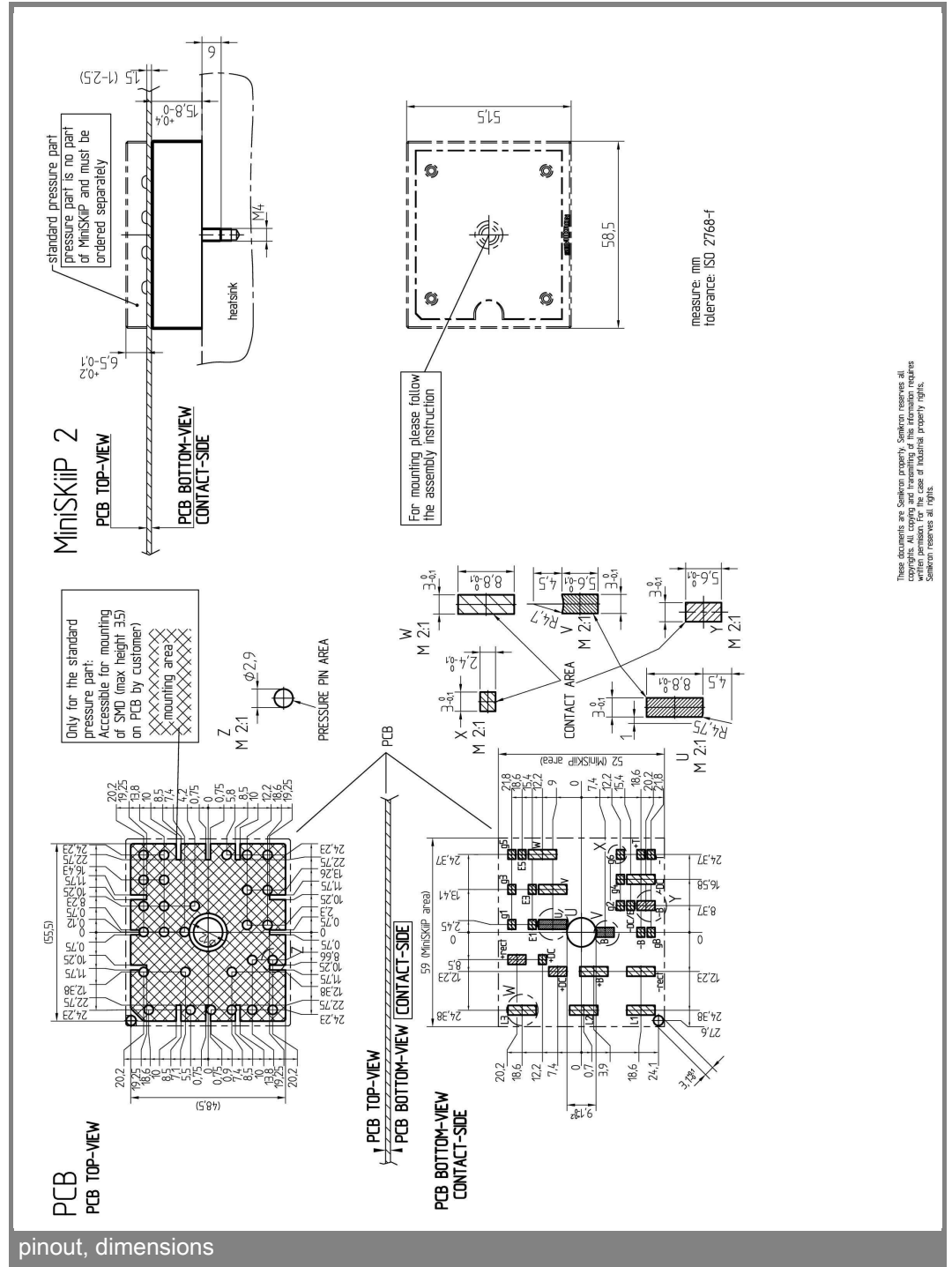
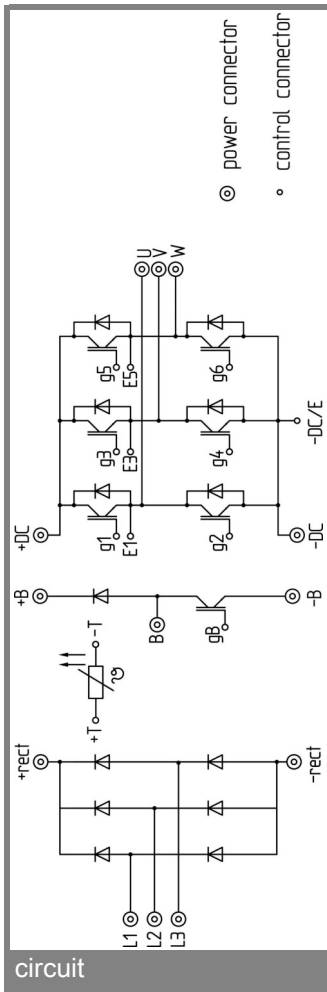


Fig. 10 Typ. input bridge forward characteristic



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.